www.elsevier.com/locate/jmmm

Micromagnetic Analysis of Fast Precessional Switching

M. d'Aquino^{a,*}, W. Scholz^b, T. Schrefl^b, C. Serpico^a, J. Fidler^b

^aDepartment of Electrical Engineering, University of Napoli "Federico II", via Claudio 21, I-80125 Italy ^bDepartment of Solid State Physics, Vienna University of Technology, Vienna, Austria

Abstract

The precessional switching process in magnetic recording thin-films is investigated by means of micromagnetic simulations. The uniform mode theory is used to predict the right time instant to switch off the field and the time tolerance which still allows successful switching. This analysis is performed for different values of applied field and anisotropy constant. We verified that the uniform mode theory provides accurate information about the tolerance on the switching time for moderately soft materials.

© 2005 Elsevier B.V. All rights reserved.

PACS: 75.60.Jk;

Keywords: Landau-Lifshitz-Gilbert equation; precessional switching; magnetization dynamics

The fast switching of magnetic thin-film media is one of the main issues in the area of magnetic data storage technologies. The conventional way to realize magnetization reversal in thin films consists of applying a sufficiently large magnetic field almost antiparallel to the initial magnetization state. If the field is strong enough and applied for sufficient time, the initial configuration becomes unstable and the magnetization is forced to switch to the reversed state which, instead, is a minimum of the free energy of the system. Thus, the resulting reversal dynamics is driven by dissipative processes. This conventional switching is often referred to as "damping switching". Recently, the precessional motion of magnetization has been used to realize the switching of thin films and particles [1,2]. In this kind of switching, the external field is applied in the film plane and is approximately orthogonal to the initial magnetization state. This field produces a torque, that pushes the magnetization out-of-plane, which creates a strong demagnetizing field, leading the magnetization to precess around it. The resulting magnetization dynamics is faster and less energy-consuming. Since this magnetization dynamics consists essentially of a

precessional motion around the strong demagnetizing field, one has to switch the field off precisely when precession has brought the magnetization state close to its reversed orientation. Therefore, the applied field pulse duration is a crucial issue, while in damping switching this does not happen. In this framework, it is important to investigate which tolerance on the choice of the pulse duration allows a successful switching. In this paper, we consider the switching process of a magnetic rectangular thin-film: the thickness is c = 5 nm, the large and short edge length are a = 500 nm and b = 250 nm, respectively. The thin-film medium has a uniaxial magneto-crystalline anisotropy. The easy axis is along the x-axis (long axis), the exchange stiffness constant is $A = 1.3 \times 10^{-11}$ J/m, the saturation polarization is $J_s = 1$ T ($M_s \approx 795$ kA/m) and the damping constant is $\alpha = 0.02$; the exchange length of the material is $l_{\rm exc} = \sqrt{(2A)/(\mu_0 M_s^2)} = 5.7$ nm. We assume that the magnetization dynamics of the thin-film is described by the Landau-Lifshitz-Gilbert equation, namely:

$$\frac{\partial \mathbf{M}}{\partial t} = -\gamma \mathbf{M} \times \mathbf{H}_{\text{eff}} + \frac{\alpha}{M_s} \mathbf{M} \times \frac{\partial \mathbf{M}}{\partial t} \quad , \qquad (1)$$

where γ is the absolute value of the gyromagnetic ratio, α is the damping constant and \mathbf{H}_{eff} is the effective field

$$\mathbf{H}_{\text{eff}}(\mathbf{M}(.)) = \mathbf{H}_m + \mathbf{H}_{\text{exc}} + \mathbf{H}_{\text{an}} + \mathbf{H}_a \quad . \tag{2}$$

 $^{^{*}}$ Corresponding author. Tel: +39 081 7683505; fax: +39 081 7683171

Email address: mdaquino@unina.it (M. d'Aquino).

In Eq. (2) \mathbf{H}_a is the applied field, \mathbf{H}_{exc} is the exchange field, \mathbf{H}_{an} the anisotropy field and \mathbf{H}_m the magnetostatic (demagnetizing) field. In micromagnetic simulations Eq. (1) is integrated numerically using a backward differentiation formula [3]. The spatial discretization is done using the finite element method on a mesh consisting of tetrahedrons with mesh edge length of 5 nm < l_{exc} . A hybrid finite element boundary element method [4] is used to solve the magnetostatic problem.

It has been shown in Ref. [5] that the precessional switching process, for similar geometry and material parameters, can be reasonably considered a quasiuniform process, so that the uniform mode theory can be applied.

For this reason, we approximate the thin-film with a flat ellipsoid characterized by the demagnetizing factors N_x , N_y , N_z such that N_x , $N_y \ll N_z \approx 1$. Since we deal with media having small dissipative effect, we can study the conservative magnetization dynamic by means of the undamped Landau-Lifshitz equation:

$$\frac{d\mathbf{m}}{dt} = -\mathbf{m} \times \mathbf{h}_{\text{eff}} \quad , \tag{3}$$

where time is measured in units of $(\gamma M_s)^{-1}$ and the (normalized) effective field $\mathbf{h}_{\text{eff}} = \mathbf{H}_{\text{eff}}/M_s$ has now the following form, provided that the exchange field is zero:

$$\mathbf{h}_{\text{eff}} = -D_x m_x \mathbf{e}_x - D_y m_y \mathbf{e}_y - D_z m_z \mathbf{e}_z + h_a \mathbf{e}_y \quad . \quad (4)$$

The coefficients $D_x < D_y < D_z$ take into account the demagnetizing effects and magnetocrystalline anisotropy, h_a is the normalized applied field and $\mathbf{e}_x, \mathbf{e}_y, \mathbf{e}_z$ are the unit vectors along the Cartesian axes x, y, z, respectively. The relationship between the material parameters and the coefficients D_x, D_y, D_z are:

$$D_x = N_x - \frac{2K_1}{\mu_0 M_s^2}, \ D_y = N_y, \ D_z = N_z.$$
 (5)

We follow now the approach proposed in Ref. [6] to derive the expression of the external field pulse duration T_s and the time window $[t_1, t_2]$ around it that leads to a successful switching. To this end we exploit the motion integrals of Eq. (3):

$$m_x^2 + m_y^2 + m_z^2 = 1 (6)$$

$$\frac{1}{2}D_xm_x^2 + \frac{1}{2}D_ym_y^2 + \frac{1}{2}D_zm_z^2 - h_am_y = g_0 , \qquad (7)$$

representing magnetization magnitude conservation and energy conservation, respectively, with g_0 being the initial energy. It has been shown in Ref. [6] that, by considering the appropriate linear combination of Eqs. (6) and (7), the precessional magnetization motion occurs along the elliptic curve:

$$m_x^2 + k^2 (m_y - a_y)^2 = p^2$$
 , (8)

confined in the unit disk $m_x^2 + m_y^2 \le 1$. In Eq. (8) $k^2 = (D_z - D_y)/(D_z - D_x), a_y = -h_a/(D_z - D_y),$

Fig. 1. Plot of switching time T_s (solid line), t_1, t_2 (dashed line). $h_a = D_y - D_x$, D_x according to Eq. (5), $D_y = 0.0175$, $D_z = 0.9763$.

 $p^2 = k^2 a_y^2 + (D_z - 2g_0)/(D_z - D_x)$. It is possible to express the elliptic curve (8) in parametric form:

$$m_x = -p\cos u \quad , \quad m_y = a_y + \frac{p}{k}\sin u \quad , \quad (9)$$

where $u \in [0, 2\pi]$ is the parameter. By substituting Eqs. (9) in Eq. (3) and separating variables one ends up with the following differential equation

$$\frac{du}{f(u)} = k(D_z - D_x)dt, \qquad (10)$$

where $f(u) = \sqrt{1 - p^2 \cos^2 u - (a_y - (p/k) \sin u)^2}$, which gives the relation between the parametric variable u and time. By using Eq. (10) it is possible to derive the following expressions for the switching time T_s and the time window $[t_1, t_2]$ for switching the applied field off such that $t_1 < T_s < t_2$:

$$t_1 = \int_{u_0}^{u_1} \frac{du}{k(D_z - D_x)f(u)} \quad , \tag{11}$$

$$t_2 = t_1 + 2 \int_{u_1}^{u_2} \frac{du}{k(D_z - D_x)f(u)} \quad , \tag{12}$$

$$T_s = (t_2 + t_1)/2$$
 . (13)

In the last equations the value of the parameters u_0 , u_2 can be found by using parametric Eqs. (9) to find the intersections between Eq. (8) and the unit circle $m_x^2 + m_y^2 = 1$. The value u_1 can be found from the intersection between Eq. (8) and the ellipse $m_x^2 + k^2 m_y^2 = k^2$ delimiting the high energy region, by using parametric Eqs. (9). The details of this analysis can be found in Ref. [6]. It is important to notice that, in the conservative case, t_1 is the time instant at which the magnetization enters the potential well around the reversed state, t_2 is the time instant at which magnetization goes out from that potential well and T_s is the time instant at which the magnetization is exactly in the reversed state. Thus, in a slightly dissipative case, switching the





Fig. 2. Plot of m_x vs time; (a) $K_1 = 10^4$; (b) $K_1 = 2.5 \times 10^4$; (c) $K_1 = 5 \times 10^4$; (d) $K_1 = 7.5 \times 10^4$; (e) $K_1 = 10 \times 10^4$. In each plot the switching time T_s is emphasized with a black dot.

applied field off when $t_1 < t < t_2$ lets the magnetization relax towards the reversed state due to the damping effect. In Fig. 1 the plot of the time instants t_1, T_s , t_2 is reported as a function of the anisotropy constant K_1 . The applied field $h_a = D_y - D_x$ is related to K_1 through Eq. (5). It is important to underline that the time window for switching the field off is reasonably wide because, in the analyzed interval of K_1 , is $t_1 <$ $0.75 \times T_s$ and $t_2 > 1.25 \times T_s$, that is, a tolerance of at least 25% on the switching time is allowed. On the basis of the above analysis we performed a set of micromagnetic simulations of precessional switching experiments. Initially, the thin-film is saturated along the positive x-axis, then it is relaxed to the remanent state. At time t = 0 the rectangular external field pulse is applied $H_a = (D_y - D_x)M_s$ until time $t = T_s$ at which the field is switched off and the magnetization relaxes towards equilibrium. We performed different simulations for different values of K_1 , reported in table below:

$K_1 \; [10^4 \; {\rm J/m^3}]$	1.0	2.5	5.0	7.5	10
$H_a \; [\rm kA/m]$	30.88	60.88	110.88	160.88	210.88
T_s [ps]	124.3	86.6	62.0	49.8	42.1
$t_1 \; [ps]$	92.9	64.6	46.0	36.7	30.9
$t_2 [\mathrm{ps}]$	155.6	108.7	78.0	62.9	53.3

The results are reported in Fig. 2 where the switching time T_s is emphasized. One can clearly see that for moderately low values of K_1 (Fig. 2a) at $t = T_s$ magnetization is not exactly close to the reversed state, but micromagnetic simulations show that the higher is the applied field strength, the better is the agreement with the uniform mode theory. By moderately increasing the value of the anisotropy constant there is a very good agreement with the above prediction and the remain-



Fig. 3. Plot of m_x vs time. The field is switched off at time (a) t = 108 ps; (b) t = 120 ps; (c) t = 65 ps; (d) t = 63 ps.

ing oscillation after $t = T_s$ tends to be very close to the magnetization reversed state (Fig. 2(b)-(e)). Next, we chose to verify the prediction of the uniform mode theory regarding the time window for switching the field off. We analyze, for sake of brevity, the case of anisotropy constant $K_1 = 2.5 \times 10^4 \text{ J/m}^3$. The applied field is $H_a = (D_y - D_x)M_s = 60.88$ kA/m. The results are reported in Fig. 3, showing the high accuracy of the uniform mode theory prediction. In fact, switching the applied field off just few picoseconds after time $t = t_2$ (Fig. 3b) or just a few picoseconds before time $t = t_1$ (Fig. 3d) leads to non-successful switching, while switching the applied field off just few picoseconds before time $t = t_2$ (Fig. 3a) or just a few picoseconds after time $t = t_1$ (Fig. 3c) leads to successful switching. The prediction applies with better accuracy with higher anisotropy constant values. Thus, we can conclude that, in precessional switching experiments on thin-film media constituted of moderately soft materials, the time window for switching the applied field off can be derived by using the uniform mode theory with a very high accuracy.

The financial support of the Italian MIUR-FIRB under contract No. RBAU01B2T8_002 and the Austrian Science Fund (Y132-N02) is acknowledged.

References

- M. Bauer, J. Fassbender, B. Hillebrands, and R. L. Stamps, Phys. Rev. B 61 (2000) 3410-3416.
- [2] S. Kaka, S. E. Russek, Appl. Phys. Lett. 80 (2002) 2958-2960.
- [3] P.N. Brown, A.C. Hindmarsh, Journal of Applied Math. Comp. 31 (1989) 40.
- [4] D.R. Fredkin, T.R. Koehler, IEEE Trans. Magn. 26 (1990) 415-417.
- [5] M. d'Aquino, W. Scholz, T. Schrefl, C. Serpico, J. Fidler, Journal of Applied Physics vol. 95, no. 11 (2004) 7055-7057.
- [6] G. Bertotti, I.D. Mayergoyz, C. Serpico, IEEE Trans. Magn. vol. 39, no. 5 (2003) 2504-2506.